

**PLEASE AMEND THE SPECIFICATION AS FOLLOWS:**

After the title, insert -- This is a continuation of Patent Application serial number 10/282,387, filing date 10/29/02, Novel Dual Gate Dielectric Scheme: SiON For High Performance Devices And High K For Low Power Devices  
, assigned to the same assignee as the present invention.

**REMARKS**

A reference to the parent case has been added by Preliminary Amendment to this Continuation.

The application is believed to be in condition for allowance. Allowance of the subject Patent Application is therefore respectfully requested.

Respectfully submitted,

A handwritten signature in black ink, appearing to read 'SBA', with a long horizontal line extending to the right.

STEPHEN B. ACKERMAN, REG. NO. 37,761